

640 nm Laser Diode, 40 mW

HL6362MG



Description

This 640 nm, 40 mW TO packaged laser diode is a compact light source that outputs a single transverse mode and is suited for a variety of applications such as a laser display, laser scanner, or a light source of optical equipment. It is packaged in a standard Ø5.6 mm TO can package and has an A pin configuration. This laser diode is compatible with our line of laser diode and TEC controllers as well as our selection of collimation solutions and TO can laser diode mounts.

Specifications

Absolute Maximum Ratings ^a				
Specification	Maximum			
Optical Output Power, CW	45 mW			
LD Reverse Voltage	2 V			
PD Reverse Voltage	30 V			
Operating Temperature	-10 °C to 50 °C			
Storage Temperature	-40 °C to 85 °C			



a. Absolute Maximum Rating specifications should never be exceeded. Operating at or beyond these conditions can permanently damage the laser.

HL6362MG Specifications ^a							
		Symbol	Min	Typical	Max		
Center Wavelength @ Pop		λο	-	640 nm	643 nm		
Optical Output Power, CW		P _{op}	-	40 mW	-		
Threshold Current		I _{TH}	-	45 mA	60 mA		
Operating Current, CW @ P _{op}		I _{op}	-	90 mA	110 mA		
Operating Voltage @ Pop		V _{op}	-	2.5 V	3.0 V		
Slope Efficiency		η	-	1.0 mW/mA	-		
Beam Divergence (FWHM) @ P _{op}	Parallel	θ,,	7°	10°	13°		
	Perpendicular	$ heta_{\perp}$	16°	21°	24°		
Monitor Current @ Pop		I_{PD}	0.15 mA	0.35 mA	0.60 mA		

a. $T_{CASE} = 25$ °C if not specified.



Drawing





